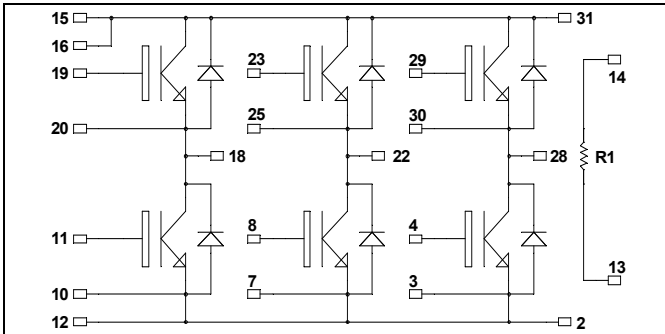
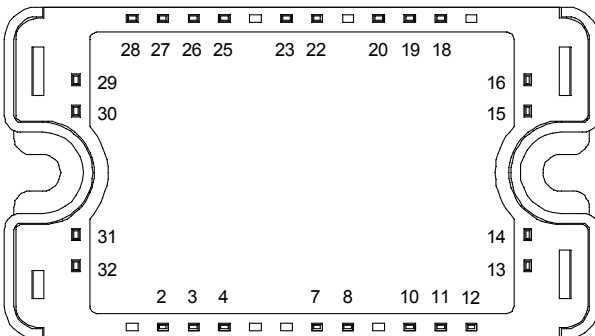


**3 Phase bridge
Trench + Field Stop IGBT®
Power Module**

**$V_{CES} = 600V$
 $I_C = 30A @ T_c = 80^\circ C$**



It is recommended to connect a decoupling capacitor between pins 31 & 2 to reduce switching overvoltages, if DC Power is connected between pins 15, 16 & 12. Pins 15 & 16 must be shorted together.



Application

- Motor control

Features

- Trench + Field Stop IGBT® Technology
 - Low voltage drop
 - Low tail current
 - Switching frequency up to 20 kHz
 - Soft recovery parallel diodes
 - Low diode VF
 - Low leakage current
 - RBSOA and SCSOA rated
- Kelvin emitter for easy drive
- Very low stray inductance
- High level of integration
- Internal thermistor for temperature monitoring

Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- RoHS compliant

Absolute maximum ratings

| Symbol | Parameter | Max ratings | Unit |
|-----------|---------------------------------------|---------------------|------------|
| V_{CES} | Collector - Emitter Breakdown Voltage | 600 | V |
| I_C | Continuous Collector Current | $T_C = 25^\circ C$ | 50 |
| | | $T_C = 80^\circ C$ | 30 |
| I_{CM} | Pulsed Collector Current | $T_C = 25^\circ C$ | 60 |
| V_{GE} | Gate - Emitter Voltage | ± 20 | V |
| P_D | Maximum Power Dissipation | $T_C = 25^\circ C$ | 90 |
| RBSOA | Reverse Bias Safe Operating Area | $T_J = 150^\circ C$ | 60A @ 550V |

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

All ratings @ $T_j = 25^\circ\text{C}$ unless otherwise specified

Electrical Characteristics

| Symbol | Characteristic | Test Conditions | Min | Typ | Max | Unit |
|---------------|--------------------------------------|---|-----|---|-----|---------------|
| I_{CES} | Zero Gate Voltage Collector Current | $V_{GE} = 0V, V_{CE} = 600V$ | | | 250 | μA |
| $V_{CE(sat)}$ | Collector Emitter Saturation Voltage | $V_{GE} = 15V$ $I_C = 30A$ | | $T_j = 25^\circ\text{C}$ 1.5 $T_j = 150^\circ\text{C}$ 1.7 | 1.9 | V |
| $V_{GE(th)}$ | Gate Threshold Voltage | $V_{GE} = V_{CE}, I_C = 400\mu\text{A}$ | 5.0 | 5.8 | 6.5 | V |
| I_{GES} | Gate – Emitter Leakage Current | $V_{GE} = 20V, V_{CE} = 0V$ | | | 300 | nA |

Dynamic Characteristics

| Symbol | Characteristic | Test Conditions | Min | Typ | Max | Unit |
|--------------|------------------------------|--|---------------------------|------|-----|------|
| C_{ies} | Input Capacitance | $V_{GE} = 0V$ | | 1600 | | pF |
| C_{oes} | Output Capacitance | $V_{CE} = 25V$ | | 110 | | |
| C_{res} | Reverse Transfer Capacitance | $f = 1\text{MHz}$ | | 50 | | |
| $T_{d(on)}$ | Turn-on Delay Time | Inductive Switching (25°C) $V_{GE} = \pm 15V$ $V_{Bus} = 300V$ $I_C = 30A$ $R_G = 10\Omega$ | | 110 | | ns |
| T_r | Rise Time | | | 45 | | |
| $T_{d(off)}$ | Turn-off Delay Time | | | 200 | | |
| T_f | Fall Time | | | 40 | | |
| $T_{d(on)}$ | Turn-on Delay Time | Inductive Switching (150°C) $V_{GE} = \pm 15V$ $V_{Bus} = 300V$ $I_C = 30A$ $R_G = 10\Omega$ | | 120 | | ns |
| T_r | Rise Time | | | 50 | | |
| $T_{d(off)}$ | Turn-off Delay Time | | | 250 | | |
| T_f | Fall Time | | | 60 | | |
| E_{on} | Turn-on Switching Energy | $V_{GE} = \pm 15V$ $V_{Bus} = 300V$ | $T_j = 25^\circ\text{C}$ | 0.16 | | mJ |
| | | | $T_j = 150^\circ\text{C}$ | 0.3 | | |
| E_{off} | Turn-off Switching Energy | $I_C = 30A$ $R_G = 10\Omega$ | $T_j = 25^\circ\text{C}$ | 0.7 | | mJ |
| | | | $T_j = 150^\circ\text{C}$ | 1.05 | | |

Reverse diode ratings and characteristics

| Symbol | Characteristic | Test Conditions | Min | Typ | Max | Unit |
|-----------|---|--|-----|---|---|---------------|
| V_{RRM} | Maximum Peak Repetitive Reverse Voltage | | 600 | | | V |
| I_{RM} | Maximum Reverse Leakage Current | $V_R = 600V$ | | | $T_j = 25^\circ\text{C}$ 250 $T_j = 150^\circ\text{C}$ 500 | μA |
| I_F | DC Forward Current | | | $T_c = 80^\circ\text{C}$ 30 | | A |
| V_F | Diode Forward Voltage | $I_F = 30A$ $V_{GE} = 0V$ | | $T_j = 25^\circ\text{C}$ 1.6 $T_j = 150^\circ\text{C}$ 1.5 | 2 | V |
| t_{rr} | Reverse Recovery Time | $I_F = 30A$ $V_R = 300V$ $di/dt = 1800A/\mu\text{s}$ | | $T_j = 25^\circ\text{C}$ 100 $T_j = 150^\circ\text{C}$ 150 | | ns |
| Q_{rr} | Reverse Recovery Charge | | | $T_j = 25^\circ\text{C}$ 1.5 $T_j = 150^\circ\text{C}$ 3.1 | | μC |
| E_r | Reverse Recovery Energy | | | $T_j = 25^\circ\text{C}$ 0.34 $T_j = 150^\circ\text{C}$ 0.75 | | mJ |
| | | | | | | |

Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

| Symbol | Characteristic | Min | Typ | Max | Unit |
|--------------------|----------------------------|-----|------|-----|------|
| R ₂₅ | Resistance @ 25°C | | 50 | | kΩ |
| B _{25/85} | T ₂₅ = 298.15 K | | 3952 | | K |

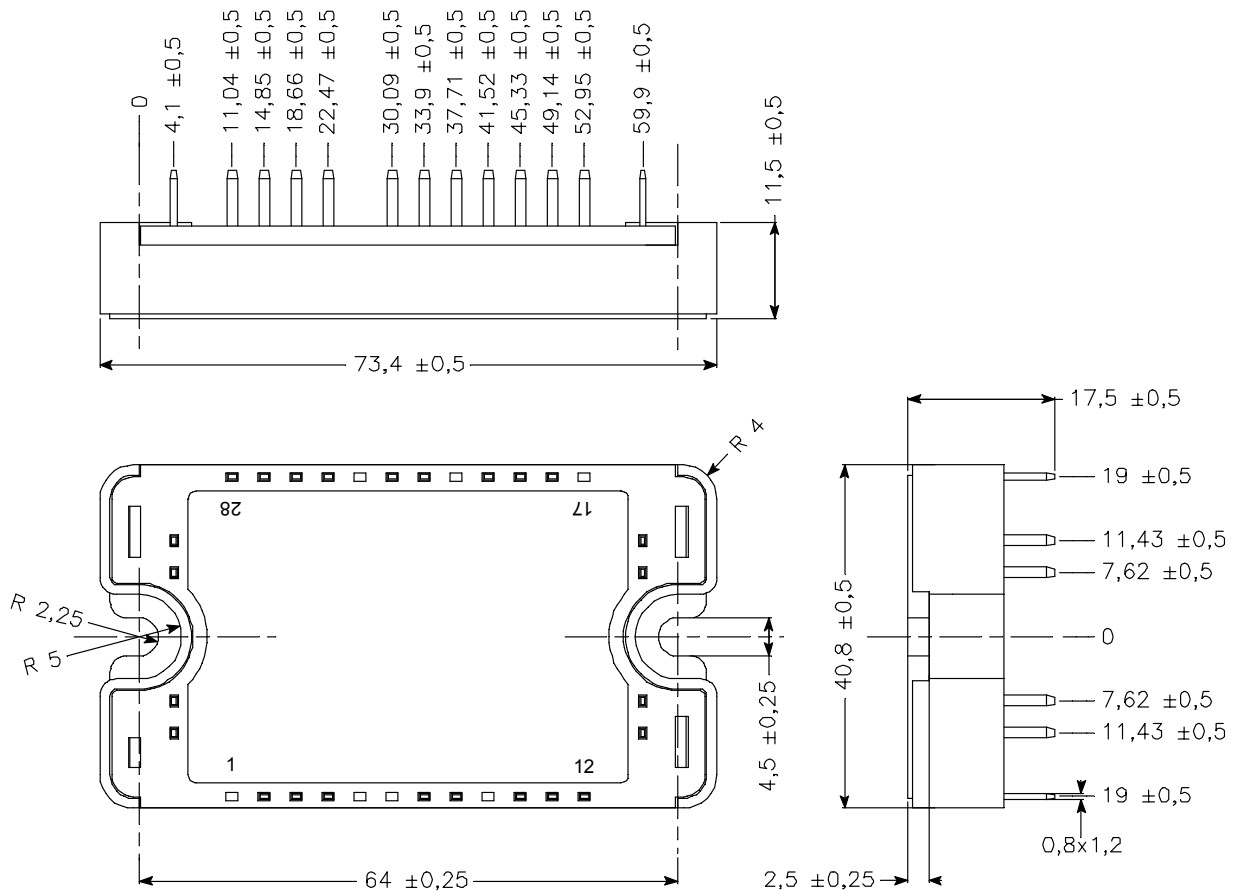
$$R_T = \frac{R_{25}}{\exp\left[B_{25/85}\left(\frac{1}{T_{25}} - \frac{1}{T}\right)\right]}$$

T: Thermistor temperature
 R_T: Thermistor value at T

Thermal and package characteristics

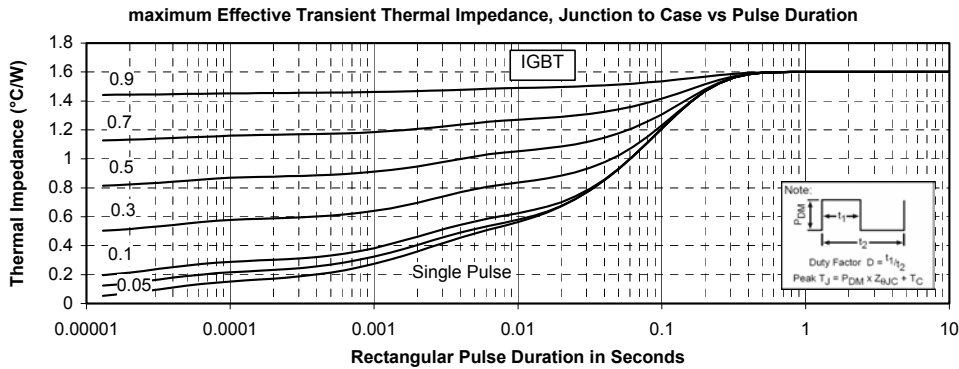
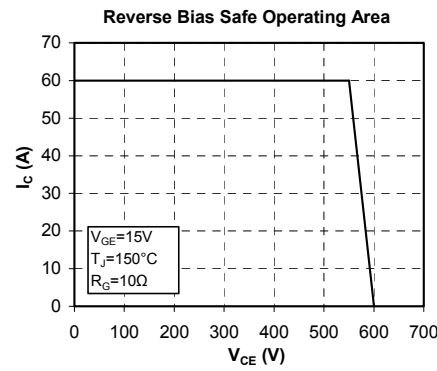
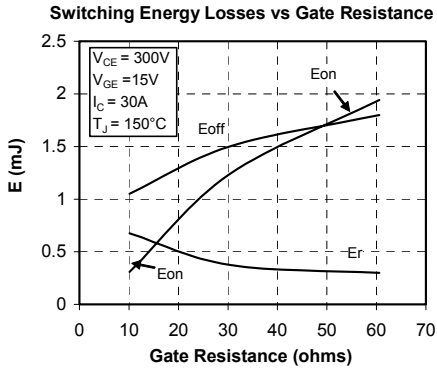
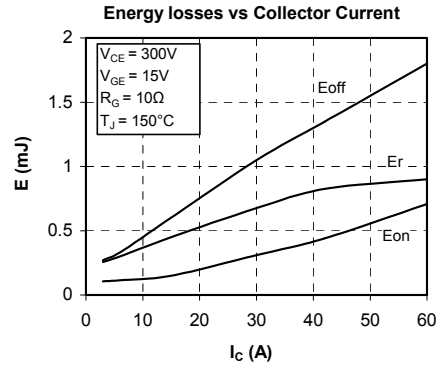
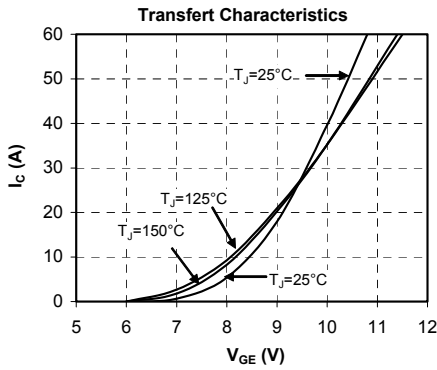
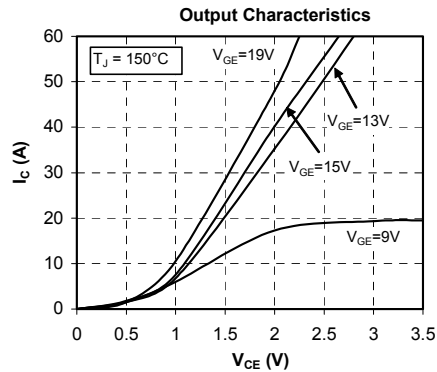
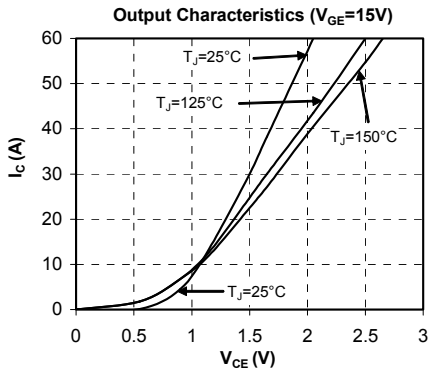
| Symbol | Characteristic | Min | Typ | Max | Unit | | |
|-------------------|--|-------|-------------|------|------|-----|-----|
| R _{thJC} | Junction to Case Thermal Resistance | IGBT | | 1.6 | °C/W | | |
| | | Diode | | 2.45 | | | |
| V _{ISOL} | RMS Isolation Voltage, any terminal to case t=1 min, I isol<1mA, 50/60Hz | 2500 | | | V | | |
| T _J | Operating junction temperature range | -40 | | 175 | °C | | |
| T _{STG} | Storage Temperature Range | -40 | | 125 | | | |
| T _C | Operating Case Temperature | -40 | | 100 | | | |
| Torque | Mounting torque | | To heatsink | M4 | 2.5 | 4.7 | N.m |
| Wt | Package Weight | | | | | 110 | g |

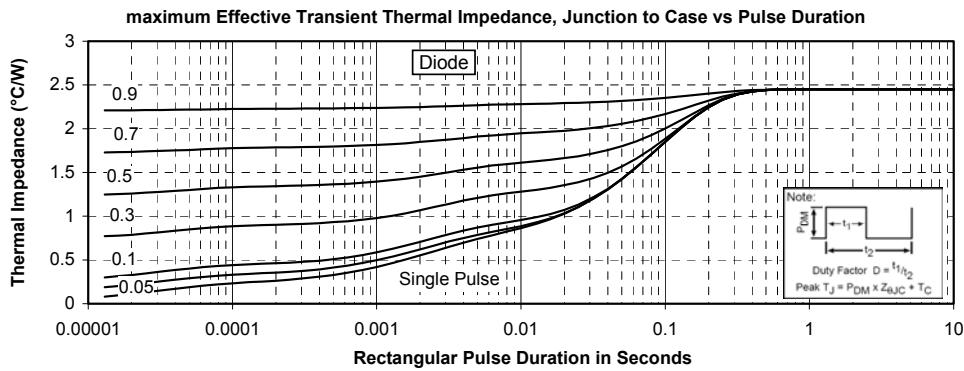
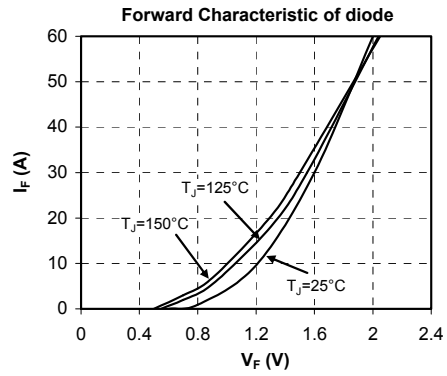
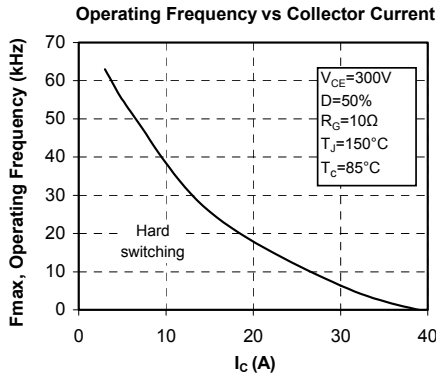
SP3 Package outline (dimensions in mm)



See application note 1901 - Mounting Instructions for SP3 Power Modules on www.microsemi.com

Typical Performance Curve





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